

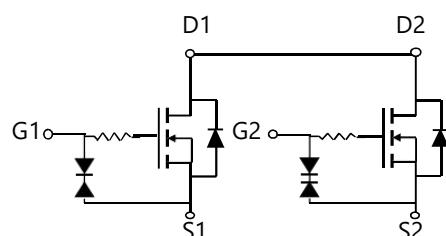
DESCRIPTION

The MX2810 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

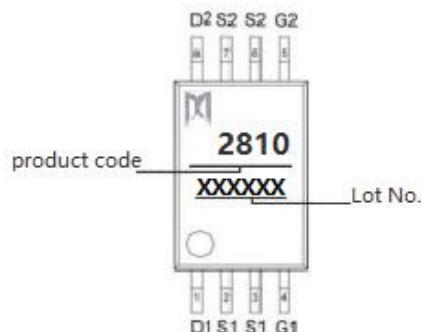
GENERAL FEATURES

- $V_{DS}=20V$, $I_D=8A$
- $R_{DS(ON)}(\text{Typ.})=18\text{m}\Omega$ @ $V_{GS}=2.5V$
- $R_{DS(ON)}(\text{Typ.})=15\text{m}\Omega$ @ $V_{GS}=3.8V$
- $R_{DS(ON)}(\text{Typ.})=13.5\text{m}\Omega$ @ $V_{GS}=4.5V$
- ESD Rating: 2000V HBM
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

PINOUT



Schematic diagram



Marking and Pin Assignment

ORDERING INFORMATION

| Part Number | Marking | Storage Temperature | Package | Devices Per Reel |
|-------------|---------|---------------------|---------|------------------|
| MX2810 | 2810 | -55°C to 150°C | TSSOP-8 | 3000 |

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------|------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate-Source Voltage | V_{GS} | ± 10 | V |
| Drain Current-Continuous | I_D | 8 | A |
| Pulsed Drain Current ^(Note1) | I_{DM} | 34 | A |
| Maximum Power Dissipation | P_D | 1.5 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | °C |

THERMAL RESISTANCE

| | | | |
|--|-----------------|------|------|
| Thermal Resistance, Junction-to-Ambient ^(Note2) | $R_{\theta JA}$ | 83.3 | °C/W |
|--|-----------------|------|------|

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.


ELECTRICAL CHARACTERISTICS($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|--------------|-------------------------------|------|------|----------|-----------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 20 | - | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=20V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 10V, V_{DS}=0V$ | - | - | ± 10 | μA |
| On Characteristics ^(Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 0.45 | 0.7 | 0.95 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=2.5V, I_D=5.5A$ | 16 | 18 | 21 | $m\Omega$ |
| | | $V_{GS}=3.8V, I_D=6A$ | 13 | 15 | 18 | $m\Omega$ |
| | | $V_{GS}=4.5V, I_D=7A$ | 12 | 13.5 | 17 | $m\Omega$ |
| Forward Transconductance | g_{FS} | $V_{DS}=5V, I_D=7A$ | - | 20 | - | S |

Dynamic Characteristics^(Note 4)

| | | | | | | |
|------------------------------|-----------|-----------------------------------|---|------|---|----|
| Input Capacitance | C_{iss} | $V_{DS}=10V, V_{GS}=0V, F=1.0MHz$ | - | 1150 | - | pF |
| Output Capacitance | C_{oss} | | - | 185 | - | pF |
| Reverse Transfer Capacitance | C_{rss} | | - | 145 | - | pF |

Switching Characteristics^(Note 4)

| | | | | | | |
|---------------------|--------------|--|---|-----|---|----|
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=10V, R_L=1.35\Omega$ $V_{GS}=5V, R_{GEN}=3\Omega$ | - | 6 | - | nS |
| Turn-on Rise Time | t_r | | - | 13 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 52 | - | nS |
| Turn-Off Fall Time | t_f | | - | 16 | - | nS |
| Total Gate Charge | Q_g | $V_{DS}=10V, I_D=7A,$ $V_{GS}=4.5V$ | - | 15 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 0.8 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 3.2 | - | nC |

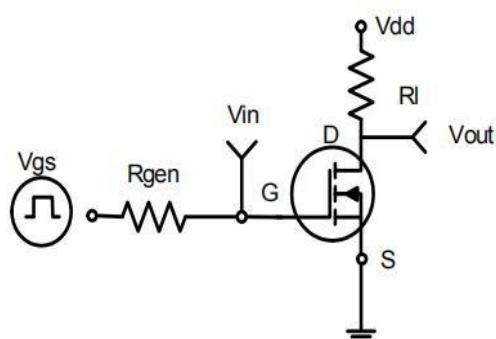
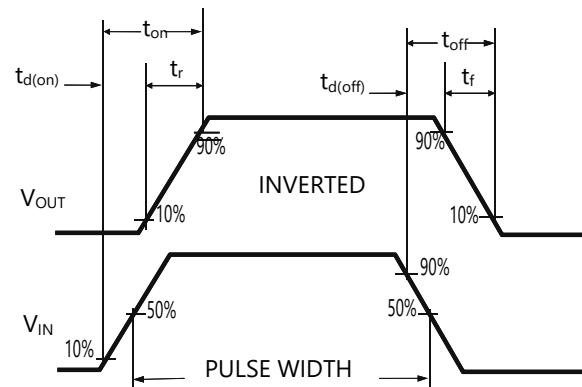
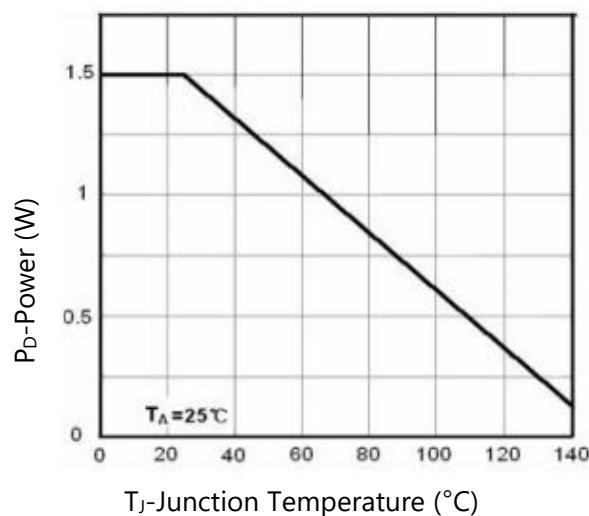
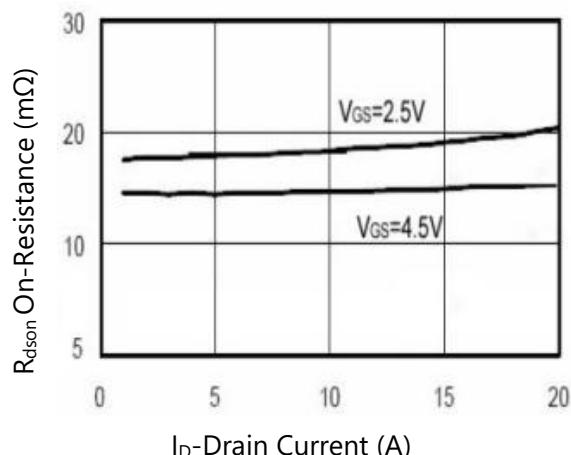
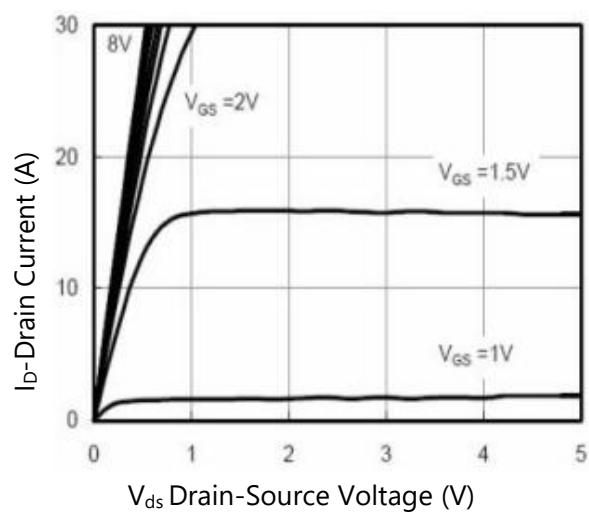
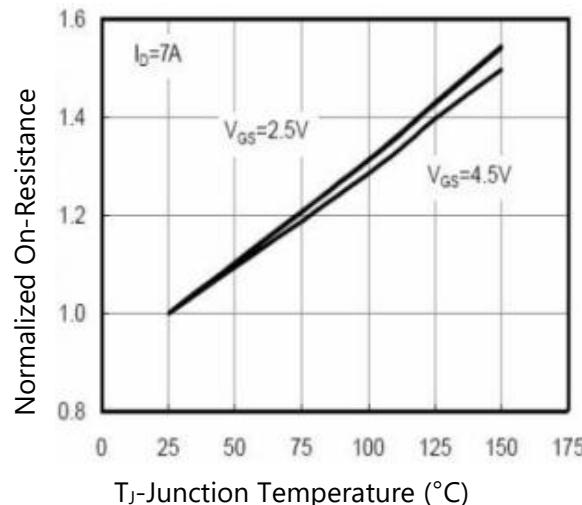
Drain-Source Diode Characteristics

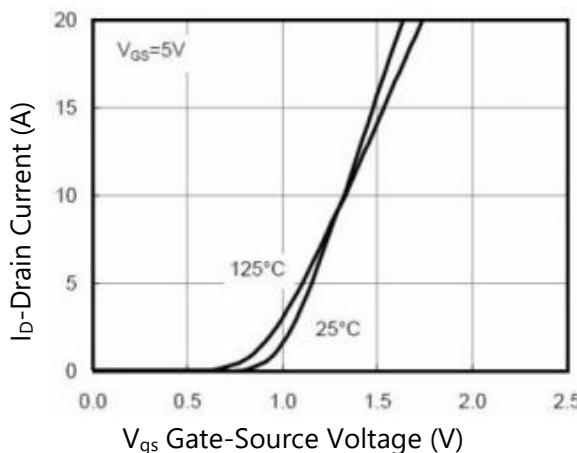
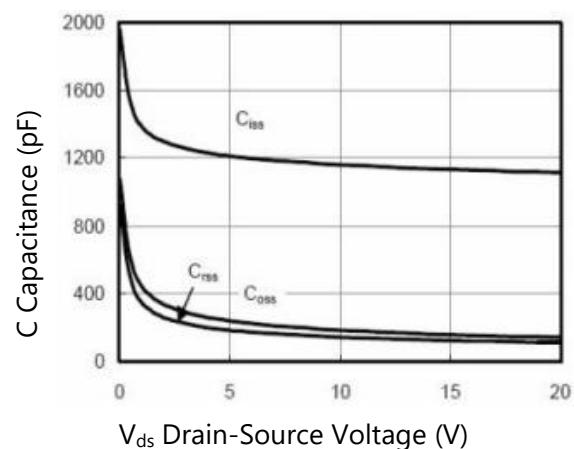
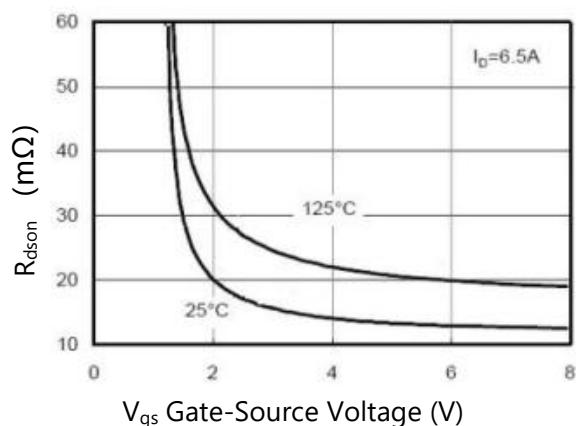
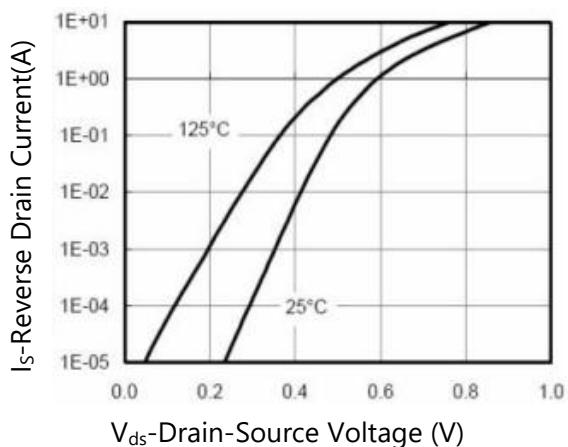
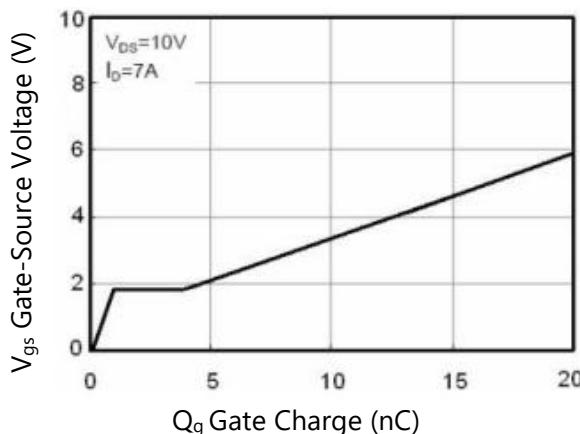
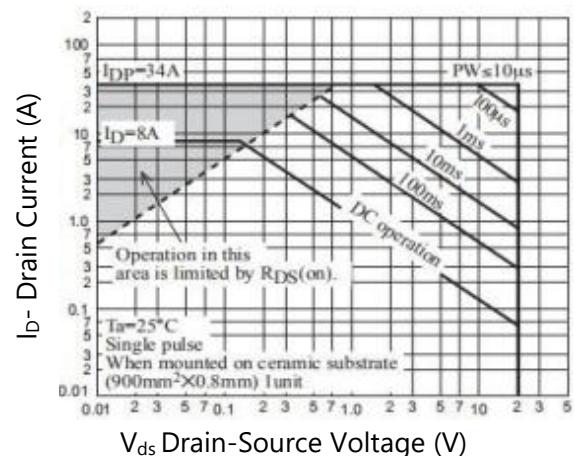
| | | | | | | |
|---|----------|---------------------|---|---|-----|---|
| Diode Forward Voltage ^(Note 3) | V_{SD} | $V_{GS}=0V, I_S=1A$ | - | - | 1.2 | V |
| Diode Forward Current ^(Note 2) | I_S | | - | - | 7 | A |

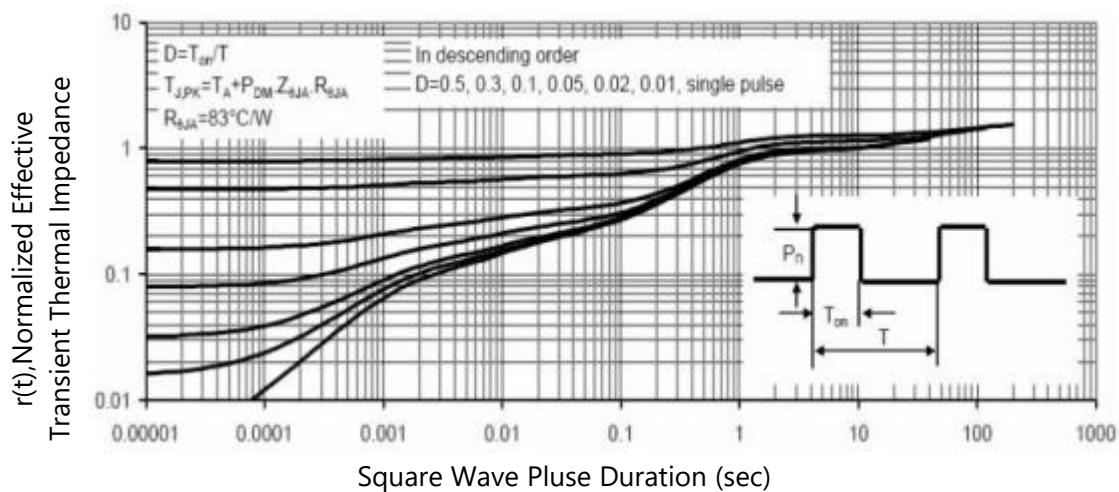
Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

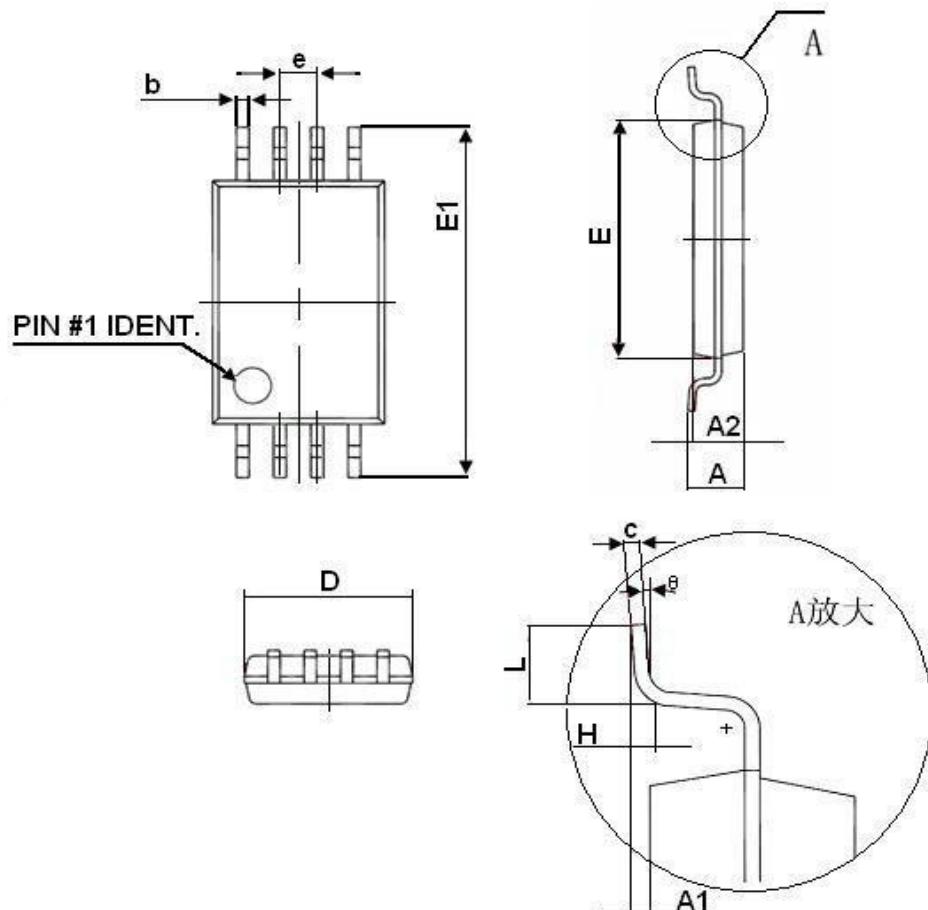
Note 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Note 4. Guaranteed by design, not subject to product.


TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 1. Switching Test Circuit

Figure 2. Switching Waveform

Figure 3. Power Dissipation

Figure 4. On-Resistance

Figure 5. Output Characteristics

Figure 6. Normalized On-Resistance



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 7. Transfer Characteristics

Figure 8. Capacitance vs V_{ds}

Figure 9. R_{dson} vs V_{gs}

Figure 10. Capacitance vs V_{ds}

Figure 11. Gate Charge

Figure 12. Safe Operation Area



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 13. Normalized Maximum Transient Thermal Impedance


PACKAGE INFORMATION
TSSOP-8


| SYMBOLS | DIMENSIONS IN MILLIMETERS | |
|---------|---------------------------|------|
| | MIN | MAX |
| D | 2.90 | 3.10 |
| E | 4.30 | 4.50 |
| b | 0.19 | 0.30 |
| c | 0.09 | 0.20 |
| E1 | 6.25 | 6.55 |
| A | - | 1.10 |
| A2 | 0.80 | 1.00 |
| A1 | 0.02 | 0.15 |
| e | 0.65(BSC) | |
| L | 0.50 | 0.70 |
| H | 0.25(TYP) | |
| θ | 1° | 7° |